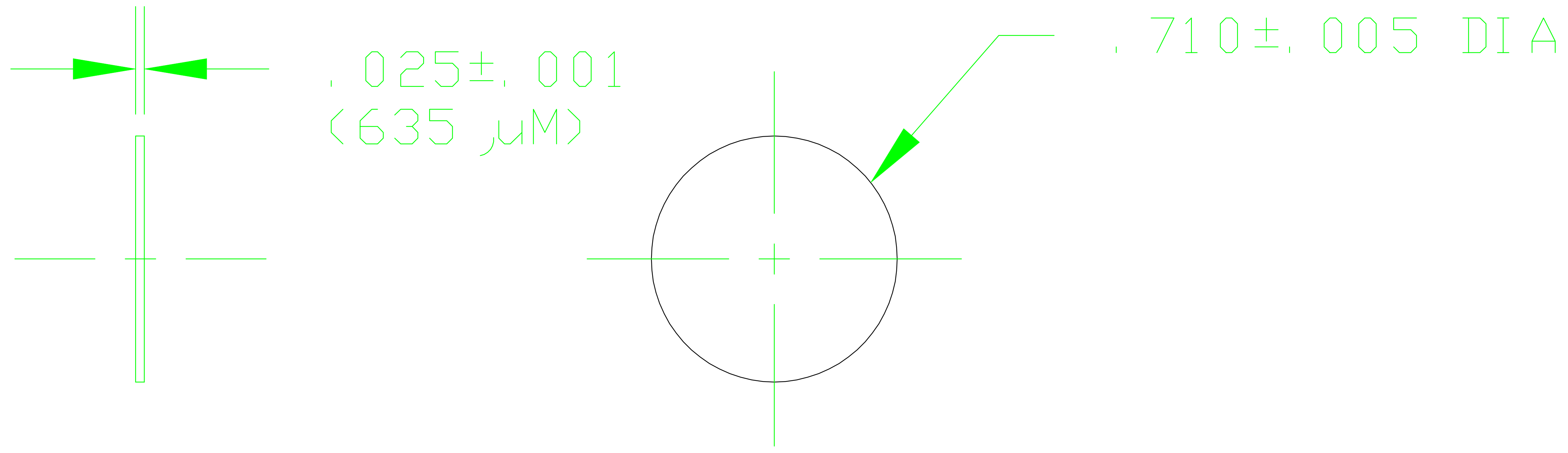
REV.	DATE	DESCRIPTION	BY	APP'D
1	10-88	REVISED NOTE 2	URIBE	



NOTES

1. MATERIAL: GALLIUM ARSENIDE

SPEC FOR:
ETCH PIT DENSITY (EPD) ≤ 10^4 /CM^2
ZINC DOPED BETWEEN 2×10^{18} AND 2×10^{19} /CM^3
RECOMMENDED VENDOR:
LASER DIODES INC.
1130 SOMERSET ST.
NEW BRUNSWICK, NJ 08901
(201)249-7000

2. CUT SO FACE OF DISK IS ORIENTED AT 2° OFF THE 100 AXIS TOWARDS THE 111A PLANE

3. POLISH ONE FACE, ETCH THE OTHER

SLAC: PF795-649-48

DRAWN BY
SPESE
CHECKED BY

APPROVED BY

NUCLEAR PHYSICS LABORATORY
UNIVERSITY OF ILLINOIS AT URBANA-CHAMPAIGN

UNLESS OTHERWISE SPECIFIED
DIMENSIONS IN INCHES 2 PLACE DEC. ±.01
BREAK SHARP CORNERS 3 PLACES DEC. ±.003
FRACTIONAL±1/32" ANGULAR±0°30'

GALLIUM ARSENIDE WAFER

PART NO.
NO. REQ'D.
CHASSIS NO. OR MATERIAL
LISTED

SCALE
2=1
DATE
7-11-88

FILE
12
DWG. NO.
C-2709-10